



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	2Ω @ $V_{GS} = 10V$	250mA
60 V	3Ω @ $V_{GS} = 5V$	250IIIA

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- **Power Management Functions**

Features

- **Dual N-Channel MOSFET**
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

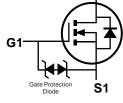
- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)





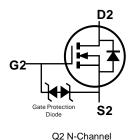
SOT363

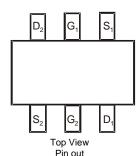




Q1 N-Channel

D1





Top View

Equivalent Circuit

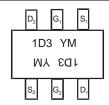
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN63D1LDW-7	SOT363	3000/Tape & Reel
DMN63D1LDW-13	SOT363	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



1D3 = Product Type Marking Code YM = Date Code Marking \overline{Y} or Y = Year (ex: B = 2014) $M = \overline{M}$ onth (ex: 9 = September)

Date Code Kev

Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	В	С	D	Е	F	G	Н		J	K	L	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	60	V	
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	250 200	mA
Maximum Continuous Body Diode Forward Current	(Note 6)	Is	0.5	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	(Note 6)		I _{DM}	1.2	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P _D	310	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	414	°C/W
Total Power Dissipation (Note 6)		P _D	390	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	324	°C/W
Operating and Storage Temperature Range	·	T _{J,} T _{STG}	-55 to +150	°C

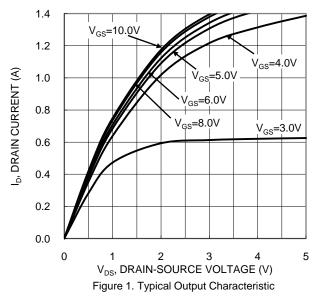
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition			
OFF CHARACTERISTICS (Note 7)	1 2		, ,,,						
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$			
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$			
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$			
ON CHARACTERISTICS (Note 7)									
Gate Threshold Voltage	V _{GS(TH)}	1.0	1.6	2.5	V	$V_{DS} = 10V, I_{D} = 1mA$			
Static Drain-Source On-Resistance		_	_	2.0	Ω	$V_{GS} = 10V, I_D = 0.5A$			
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	3.0	12	$V_{GS} = 5V, I_D = 0.05A$			
Forward Transfer Admittance	Y _{fs}	80	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$			
Diode Forward Voltage	V_{SD}	_	0.75	1.1	V	$V_{GS} = 0V, I_{S} = 115mA$			
DYNAMIC CHARACTERISTICS (Note 8)									
Input Capacitance	C _{iss}	_	30	_	pF	V 05V V 0V			
Output Capacitance	Coss	_	4.2	_	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz			
Reverse Transfer Capacitance	C _{rss}	_	2.9	_	pF	1 = 1.0101112			
Gate Resistance	R_{g}	_	133	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$			
Total Gate Charge	Qq	_	304	_	рC	45)/)/ 40)/			
Gate-Source Charge	Q _{gs}	_	203	_	рC	$V_{GS} = 4.5V, V_{DS} = 10V,$			
Gate-Drain Charge	Q _{qd}	_	84	_	рС	I _D = 250mA			
Turn-On Delay Time	t _{D(ON)}	-	3.9	_	ns				
Turn-On Rise Time	t _R	_	3.4	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$			
Turn-Off Delay Time	t _{D(OFF)}	-	15.7	_	ns	$R_G = 25\Omega$, $I_D = 200 \text{mA}$			
Turn-Off Fall Time	t _F	_	9.9	_	ns				

Notes: 5

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.





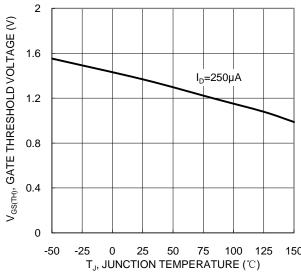
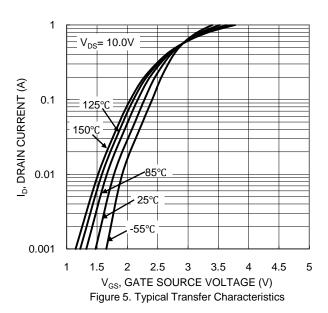


Figure 3. Gate Threshold Variation with Temperature



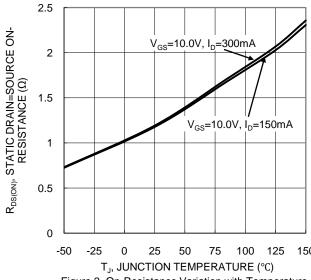


Figure 2. On-Resistance Variation with Temperature

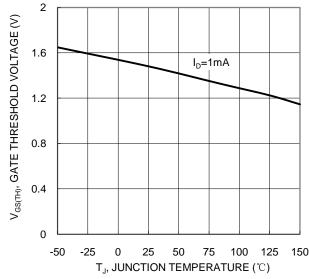


Figure 4. Gate Threshold Variation with Temperature

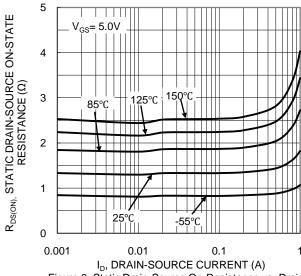


Figure 6. Static Drain-Source On-Resistance vs. Drain
Current



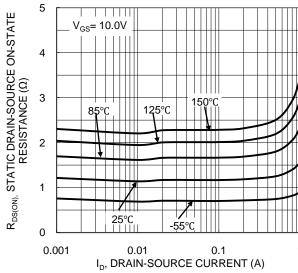
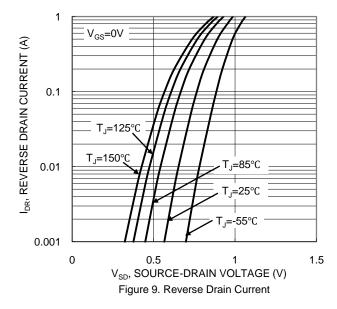
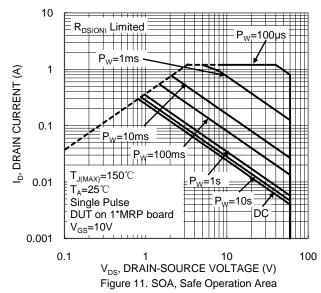


Figure 7. Static Drain-Source On-Resistance vs. Drain Current





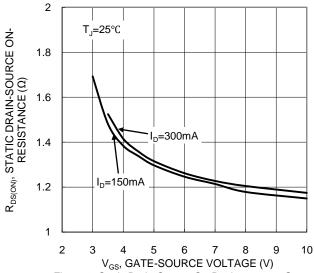
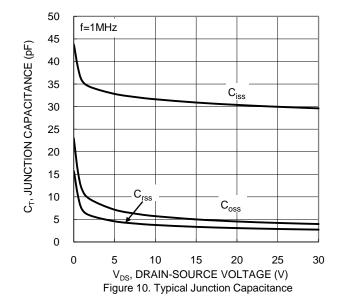
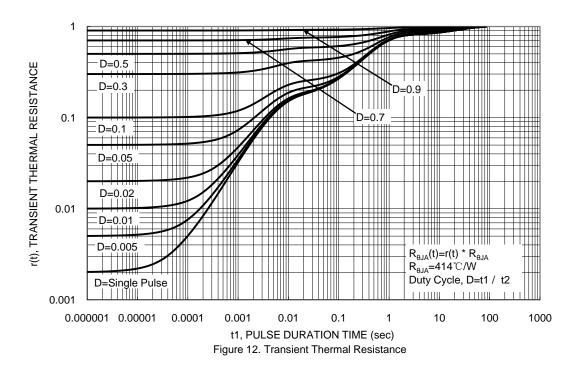


Figure 8. Static Drain-Source On-Resistance vs. Gate-Source Voltage

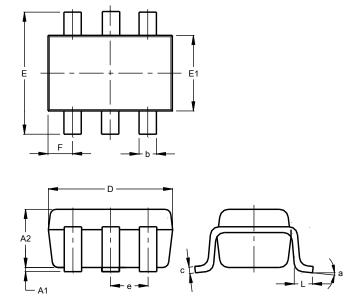






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

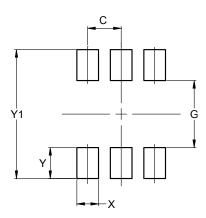


SOT363								
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.90	1.00	1.00					
b	0.10	0.30	0.25					
С	0.10	0.22	0.11					
D	1.80	2.20	2.15					
Е	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	0.650 BSC							
F	0.40	0.45	0.425					
L	0.25	0.40	0.30					
а	a 8°							
All Dimensions in mm								



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
X	0.420
Υ	0.600
Y1	2.500

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